

FEATURES	ET101	ET2000	ET3000	ET3000EXT	ET6000
Maximum Substrate Area	25 mm x 50 mm	50 mm x 50 mm	100 mm x 100 mm (opt. wafer boat)	150 mm x 150 mm (opt. wafer boat)	200 mm diameter (wafer boat up to 100)
CVDWinPrC™ Process Control	✓	✓	✓	✓	✓
Safety System	✓	✓	✓	✓	✓
Exhausted Metal Enclosure	✓	✓	✓	✓	✓
Mass Flow Controlled Gas Lines	Up to 8	Up to 8	Up to 12	Up to 16	6 per tube
External Vapor Delivery System (eg. bubbler)	Up to 3	Up to 3	Up to 4	Up to 4	1 per tube
Internal Vapor Delivery System	N/A	Optional	Optional	Optional	Optional
Air to Water Heat Exchanger	N/A	Optional	Optional	Optional	Optional
Process Support Demo (CVD Lab or On-site)	Optional	Optional	Optional	Optional	Optional
Factory Training	✓	✓	✓	✓	✓
On-Site Startup Assistance	✓	✓	✓	✓	✓
Heating:					
Resistance Hotwall 1100 °C	✓	✓	✓	✓	✓
Resistance Hotwall 1200 °C	Optional	Optional	Optional	Optional	Optional
Rolling Resistance Furnace	N/A	N/A	N/A	Optional	N/A
Infrared Coldwall 1100 °C	N/A	Optional	Optional	Optional	N/A
Substrate Heater Coldwall 400 °C (for PECVD)	N/A	Optional	N/A	N/A	N/A
Substrate Heater Coldwall up to 2200 °C	N/A	N/A	Optional	Optional	N/A
RF Induction Coldwall > 1500 °C	N/A	N/A	Optional	Optional	N/A
Vacuum:					
None (ATM operation)	✓	✓	✓	✓	✓
Wet Pump (Fomblin Prepared)	Optional	Optional	Optional	Optional	Optional
Dry Pump	Optional	Optional	Optional	Optional	Optional
High / Ultra-High Vacuum	Optional	Optional	Optional	Optional	Optional
Plasma	N/A	Optional	Optional	Optional	N/A
Remote Upstream Plasma	N/A	N/A	Optional	Optional	N/A
DC Substrate Bias	N/A	Optional	Optional	Optional	N/A
Wafer Rotation	N/A	Optional	Optional	Optional	N/A
Loadlock	N/A	N/A	N/A	Optional	N/A
Glovebox	N/A	N/A	Optional	Optional	N/A
Residual Gas Analyzer	Optional	Optional	Optional	Optional	Optional
Air Pump	Optional	Optional	Optional	Optional	Optional
System Size (W x L x H)	40" x 49" x 60"	30" x 64" x 60"	33" x 96" x 70"	40" x 119" x 70"	43" x 118" x 90"

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Carbon Nanotubes	✓	✓	✓	✓	✓
Graphene	✓	✓	✓	✓	N/A
2D Materials (TMDs, h-BN, etc)	✓	✓	✓	✓	✓
Semiconducting Nanowires (Si, Ge, ZnO, GaN, etc)	✓	✓	✓	✓	✓
Transparent Conductive Oxide (SnO:F, ZnO:B, etc)	✓	✓	✓	✓	N/A
Epitaxial Deposition	✓	✓	✓	✓	N/A
Atmospheric Pressure CVD (APCVD)	✓	✓	✓	✓	✓
Low Pressure CVD (LPCVD)	✓	✓	✓	✓	✓
Metal Organic CVD (MOCVD)	✓	✓	✓	✓	✓
Plasma Enhanced CVD (PECVD, PACVD, ICP-CVD)	N/A	✓	✓	✓	N/A
Rapid Thermal Processing (RTP)	N/A	✓	✓	✓	N/A
Chemical Vapor Infiltration (CVI)	✓	✓	✓	✓	✓
Fluidized Bed CVD (FBCVD, FBR)	N/A	✓	✓	✓	N/A
Atomic Layer Deposition (ALD)	✓	✓	✓	✓	N/A
Dry Oxidation	N/A	N/A	✓	✓	✓
Wet Oxidation	✓	✓	✓	✓	✓
Pyrogenic Oxidation	N/A	N/A	N/A	✓	✓
Diffusion	✓	✓	✓	✓	✓
Silicon Nitride	✓	✓	✓	✓	✓
Polysilicon	✓	✓	✓	✓	✓
Silicon Dioxide	✓	✓	✓	✓	✓
Annealing	✓	✓	✓	✓	✓



All systems include CVDWinPrC™ system control software, comprehensive software and hardware safety interlocks, preprogrammed process recipes, and startup support. Other configurations available, consult factory for details.